

		Characteristics @ If = 100 mA				
Description	Part No.	Po (mW) Typ	Vf Max (V)	Wavelength	2Θ1/2	Figure
Infrared Emitters						
2.0 mm dia. Side View	IEFB0212	10	2	880	30.0	1
	IEGB0212	4	1.7	940	30.0	
T-1, 3 mm Round	IEFB0241	35	2	880	30.0	2
	IEGB0241	10	1.7	940	30.0	
T-1-3/4, 5 mm Round	IEHB0431	50	1.6	840	30.0	3
	IEFB0431	35	2	880	30.0	
	IEGB0431	10	1.7	940	30.0	
Same in TO-18 Package	IEGB0442	12.5	1.7	940	20.0	4
Phototransistors						
		Oper. Parameters				
	Part No.	IL	Vce (Sat)	ID/Vce(nA)	2Θ1/2	Figure
(IL @ Vce=5 Volt, Ev=1000 Lux or Ee=20 mW/sq. cm. when marked w/*)						
2.0 mm dia. Side View	IPT0212	0.8-15	0.4 V	100/10	25.0	1
T-1, 3 mm Round	IPT2152	1.0-20	0.4 V	100/10	20.0	2
T-1-3/4, 5 mm Round	IPT4153	1.0-20	0.4 V	100/10	24.0	13
Same in TO-18 Package	IPT0442	1-15,Ev=200	0.4 V	200/10	15.0	4
Photodiodes						
	(IL is short circuit current @ Ev=1000 Lux or Ee=0.5 mW/sq. cm. when marked w/*)					
2.0 mm dia. Side View	IPD0212	10	Vop = 0.4 V	100	25.0	1
Black Resin Packages	IPD4308	2*	Vop = 0.4 V	30	60.0	5
	IPD6308	2*	Vop = 0.4 V	30	60.0	6
Photo Interrupters						
PCB Mount	IPI506	IRED Vf @ If = 30 mA		1.2 V typ, 1.5V max 10 mA max 100 nA max Min @ If=20 mA, Vce=5V 5 mS @Ic=2 mA, RI=100 ohm 5 mS @Ic=2 mA, RI=100 ohm	7	
	IPI507	IRED Ir @ Vr = 4 V			8	
	IPI509	"Id @ Vce=10V, If=0 " "Output Current, Ic=0.5 mA"			9	
With tab for screw mount	IPI508	"Rise time, Tr (10 to 90%) " "Fall time, Tf (90 to 10%) "			10	
	IPI508P				11	
	IPI510				12	

* Specifications subject to change without notice. Dimensions are in mm±0.3 unless stated otherwise.

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